

AMENDMENTS TO THE SPECIFICATION:

Page 3, replace the paragraph beginning on line 10 with the following amended paragraph:

--However, as shown in FIGS. 4B, 4C, the solid state image sensor manufactured using the conventional method is constructed such that particularly, an extremely small spacing is created between the shift register electrodes 830 in the peripheral area after deposition of the interlayer insulation film 806, and therefore, formation of the metal interconnect lines 808 in the peripheral area potentially results in an open circuit 809 due to poor step coverage of the associated metal films over an underlying step, unfavorably causing the image sensor to have deteriorated charge transfer ability. Moreover, when the interlayer insulation film 806 interposed between the metal interconnect lines 808 and diffusion layers, polysilicon electrodes in the peripheral area is thin, parasitic capacitance therebetween becomes large and then causes increase in power consumption of image sensor.--